

3N246

MINIATURE INTEGRAL DIODE ASSEMBLIES

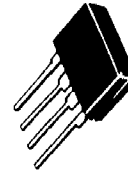
... with silicon rectifier chips interconnected and encapsulated into voidless rectifier bridge circuits.

- High Resistance to Shock and Vibration
- High Dielectric Strength
- Built-In Printed Circuit Board Stand-Offs
- UL Recognized
- $RO_{JA} = 60^{\circ}\text{C}/\text{W}$



SINGLE-PHASE
FULL-WAVE BRIDGE

1.0 AMPERE
50-1000 VOLTS



MAXIMUM RATINGS		3N246		Unit
Rating (Per Diode)	Symbol			
Peak Repetitive Reverse Voltage	VRRM	50		Volts
Working Peak Reverse Voltage	VRWM			
DC Blocking Voltage	VR			
DC Output Voltage	Vdc	32		Volts
Resistive Load	Vdc	50		Volts
Capacitive Load				
Sine Wave RMS Input Voltage	VR(RMS)	35		Volts
Average Rectified Forward Current (single phase bridge operation, resistive load, 60 Hz, $T_A = 75^{\circ}\text{C}$)	I_O	1.0		Amp
Non-Repetitive Peak Surge Current (Preceded and followed by rated current and voltage, $T_A = 75^{\circ}\text{C}$)	I_{FSM}	30 (for 1 cycle)		Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150		$^{\circ}\text{C}$

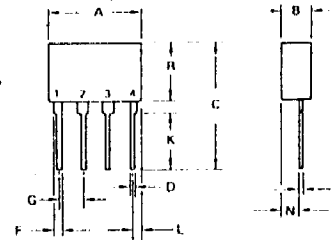
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) ($I_F = 1.57$ Amp, $T_J = 25^{\circ}\text{C}$)	v_f	1.15	1.3	Volts
Reverse Current (Per Diode) (Rated V_R , $T_A = 25^{\circ}\text{C}$)	I_R		10	μA

MECHANICAL CHARACTERISTICS

CASE: Transfer Moulded Plastic
POLARITY: Terminal-designation on case
Pin 1 (+) for DC output
Pin 4 (-) for DC output
Pins 2 and 3 (AC) for AC input

MOUNTING POSITION: Any
WEIGHT: 1.8 grams (approx)
TERMINALS: Readily solderable
connections, corrosion resistant.



STYLE 1.

TERM 1. POS
2. AC
3. AC
4. NEG

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	14.99	15.49	0.590	0.610
B	4.57	5.08	0.180	0.200
C		20.57		0.810
D	0.76	1.02	0.030	0.040
F	1.02	1.27	0.040	0.050
G	3.68	3.94	0.145	0.155
J	0.56	0.71	0.022	0.028
K		9.07		0.355
L	1.78	2.03	0.070	0.080
N	2.54	2.79	0.100	0.110
R	9.40	10.03	0.370	0.395

